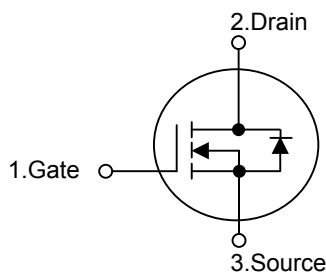


**3N60A****Power MOSFET****3A, 600V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **3N60A** is a high voltage and high current power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used in the high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

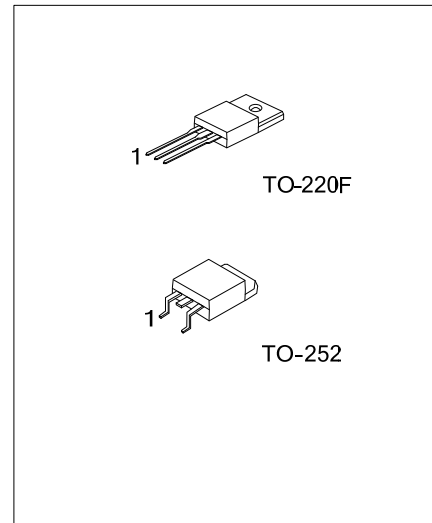
- * $V_{DS} = 600V$, $I_D = 3A$
- * $R_{DS(ON)} = 3.6\Omega$ @ $V_{GS} = 10V$
- * Ultra low gate charge (typical 10 nC)
- * Low reverse transfer capacitance ($C_{RSS} =$ typical 5.5 pF)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
3N60AL-TF3-T	3N60AG-TF3-T	TO-220F	G	D	S	Tube
3N60AL-TN3-R	3N60AG-TN3-R	TO-252	G	D	S	Tape Reel
3N60AL-TN3-T	3N60AG-TN3-T	TO-252	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

3N60AL-TF3-T (1)Packing Type (2)Package Type (3)Lead Free	(1) R: Tape Reel, T: Tube (2) TF3: TO-22F, TN3: TO-252 (3) G: Halogen Free, L: Lead Free
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■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	3.0	A
Continuous Drain Current		I_D	3.0	A
Pulsed Drain Current (Note 2)		I_{DM}	12	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	200	mJ
	Repetitive (Note 2)	E_{AR}	7.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F	P_D	34	W
	TO-252		50	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Note: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 64\text{mH}$, $I_{AS} = 2.4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 3.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

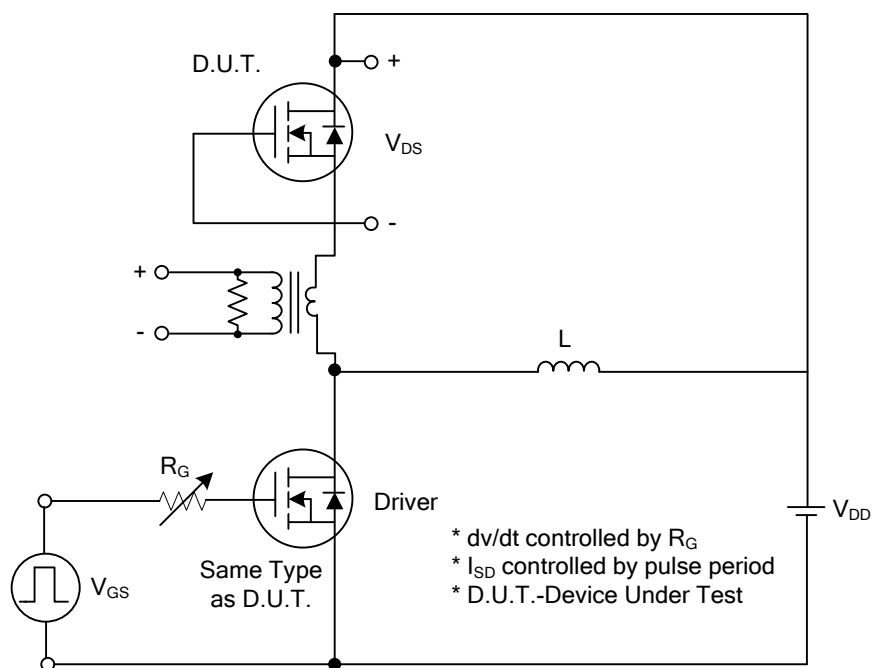
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-252		110	
Junction to Case	TO-220F	θ_{JC}	3.68	$^\circ\text{C}/\text{W}$
	TO-252		2.5	

■ ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

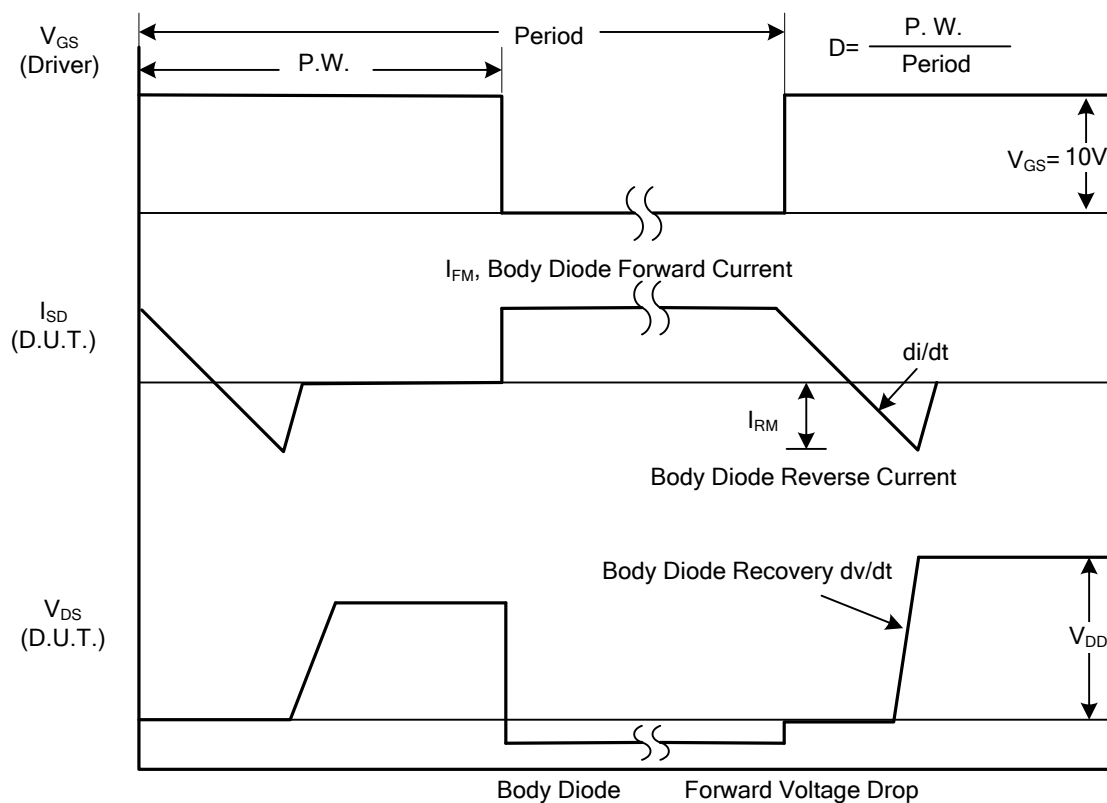
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600			V
Drain-Source Leakage Current		I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$			100	nA
	Reverse		$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$		2.8	3.6	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		350	450	pF
Output Capacitance		C_{OSS}			50	65	pF
Reverse Transfer Capacitance		C_{RSS}			5.5	7.5	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	$V_{DD} = 300\text{ V}, I_D = 3.0\text{ A},$ $R_G = 25\Omega$ (Note 1, 2)		10	30	ns
Turn-On Rise Time		t_R			30	70	ns
Turn-Off Delay Time		$t_{D(OFF)}$			20	50	ns
Turn-Off Fall Time		t_F			30	70	ns
Total Gate Charge		Q_G	$V_{DS} = 480\text{ V}, I_D = 3.0\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 1, 2)		10	13	nC
Gate-Source Charge		Q_{GS}			2.7		nC
Gate-Drain Charge		Q_{DD}			4.9		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I_S				3.0	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				12	A
Reverse Recovery Time		t_{RR}	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A},$		210		ns
Reverse Recovery Charge		Q_{RR}	$di_F/dt = 100\text{ A}/\mu\text{s}$ (Note 1)		1.2		μC

Notes: 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

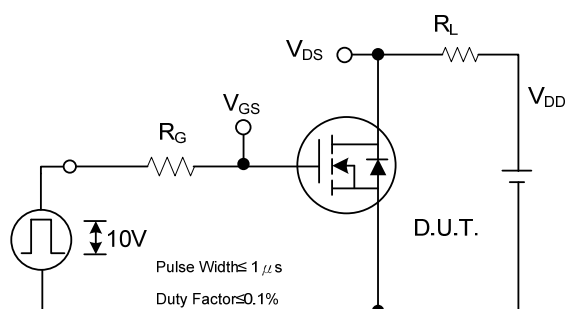


Peak Diode Recovery dv/dt Test Circuit

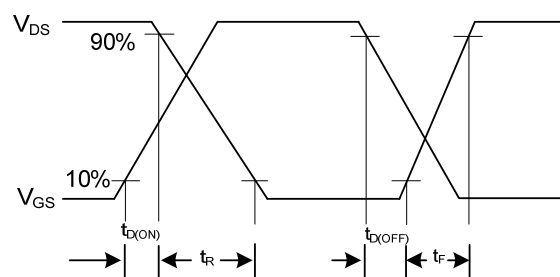


Peak Diode Recovery dv/dt Waveforms

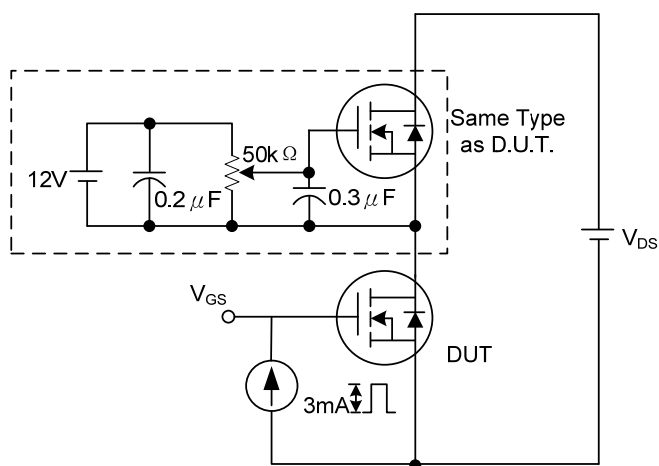
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



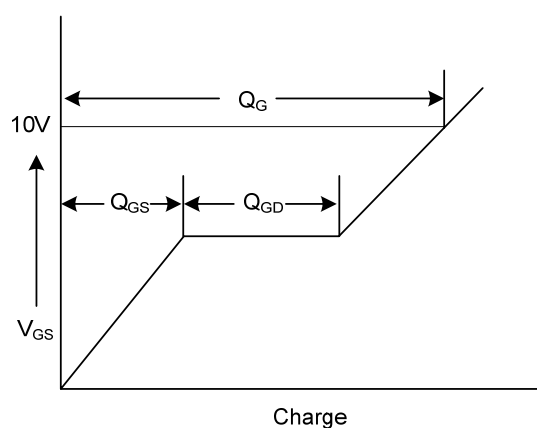
Switching Test Circuit



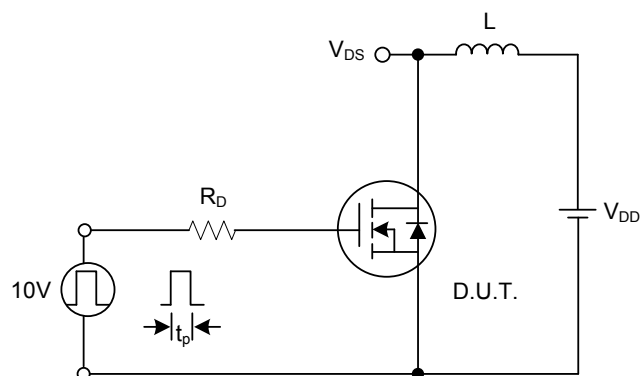
Switching Waveforms



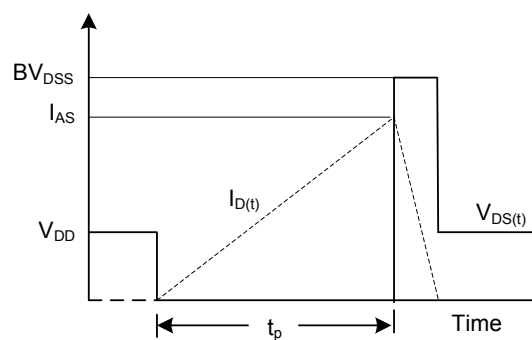
Gate Charge Test Circuit



Gate Charge Waveform



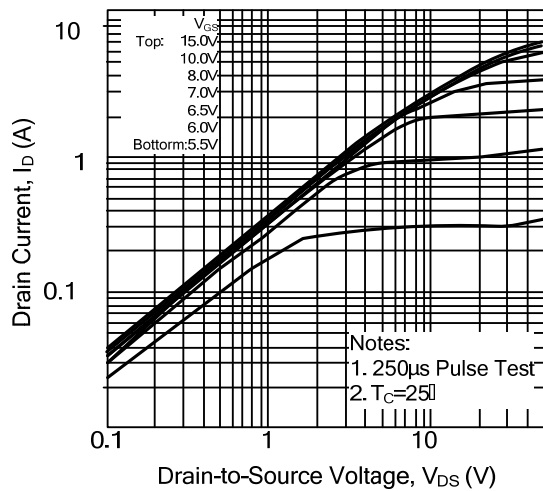
Unclamped Inductive Switching Test Circuit



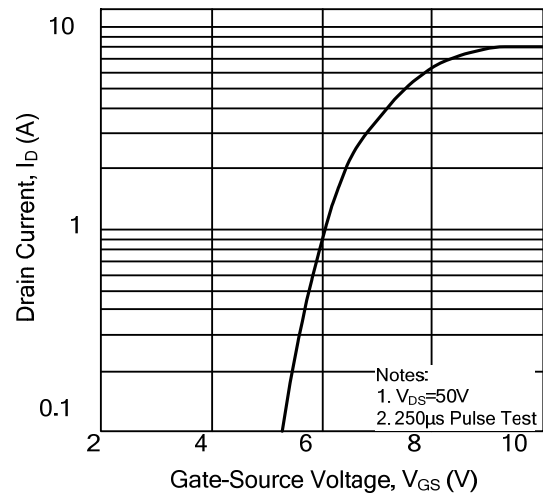
Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

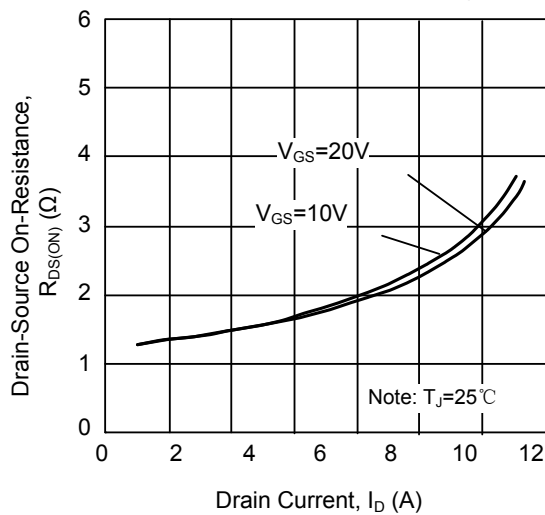
On-State Characteristics



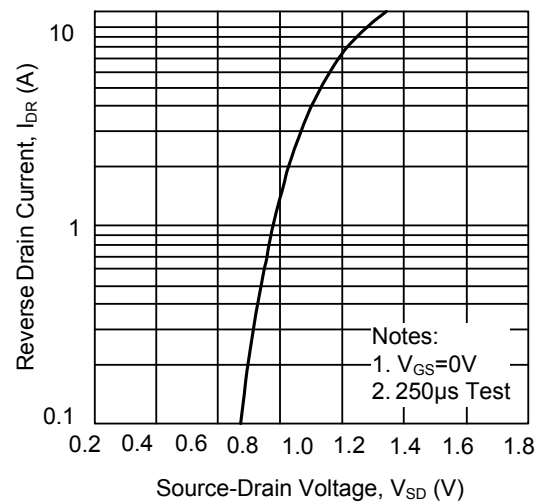
Transfer Characteristics



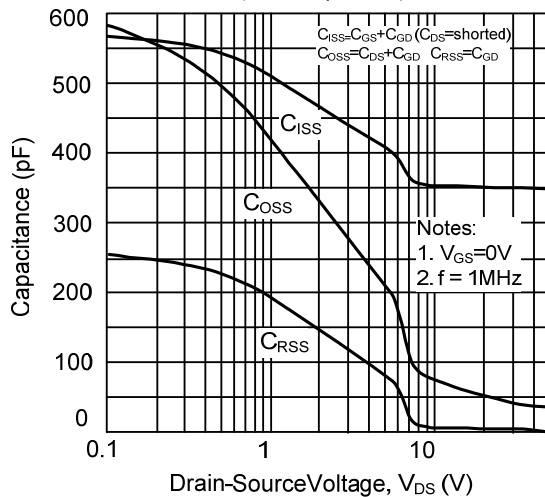
On-Resistance Variation vs. Drain Current and Gate Voltage



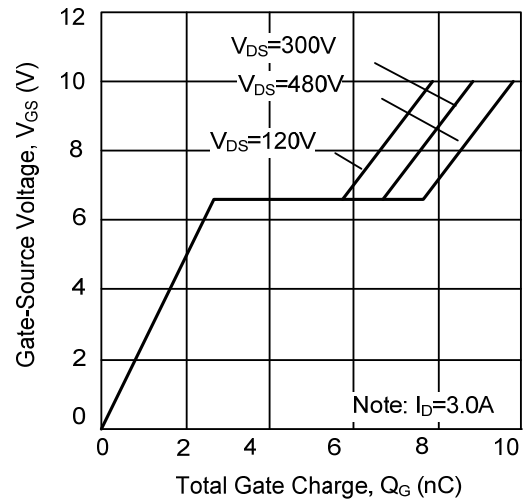
On State Current vs. Allowable Case Temperature



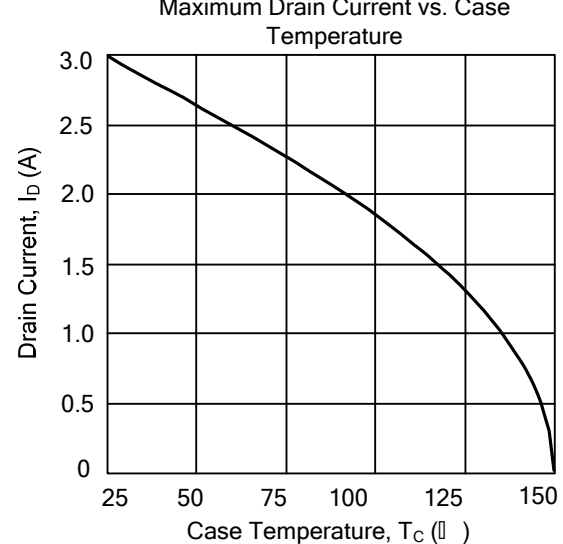
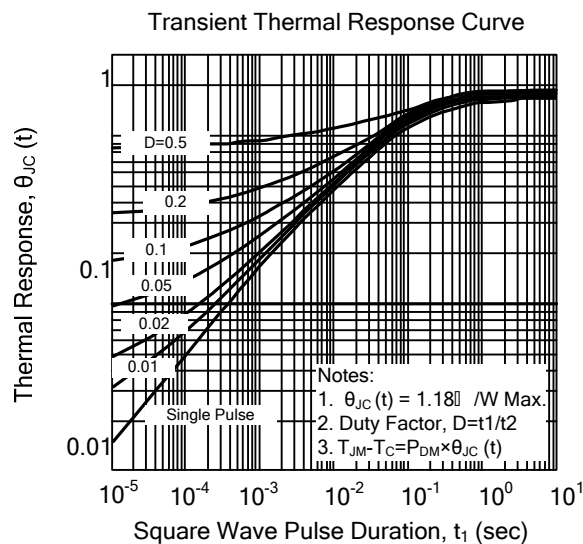
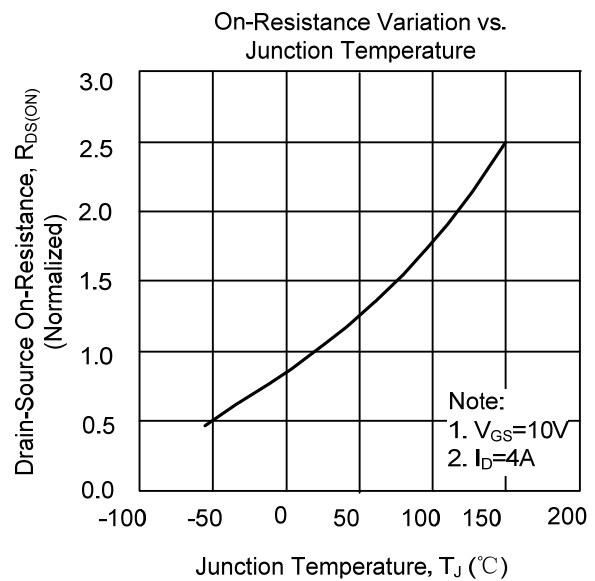
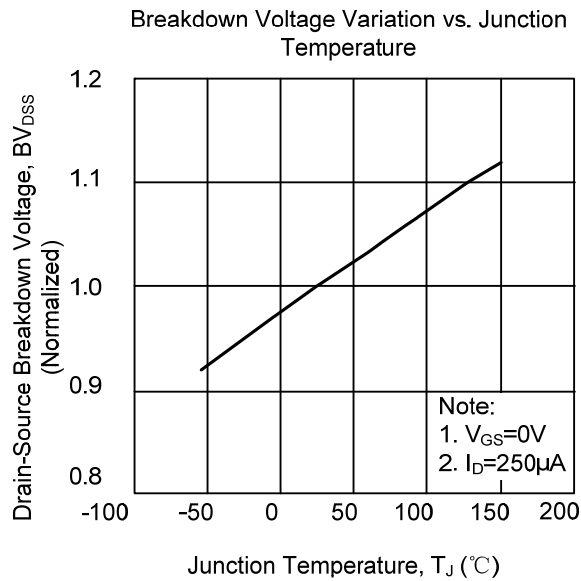
Capacitance Characteristics (Non-Repetitive)



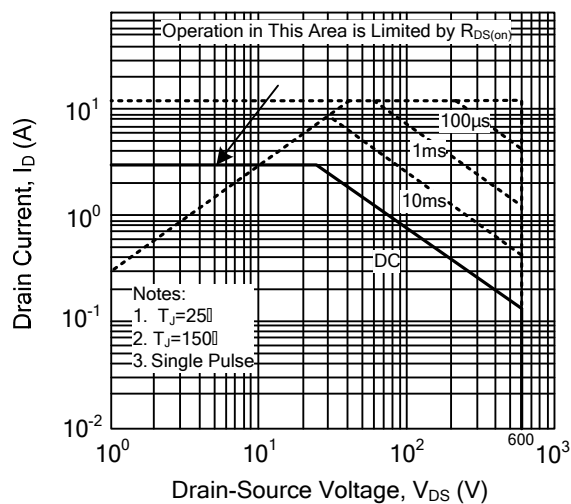
Gate Charge Characteristics



TYPICAL CHARACTERISTICS(Cont.)



Safe Operating Area - 600V



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